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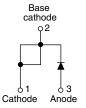
# Hyperfast Rectifier, 8 A FRED Pt®



TO-220AC



TO-220 FULL-PAK





VS-8ETH06PbF **VS-8ETH06-N3** 

VS-8ETH06FPPbF VS-8ETH06FP-N3

PRODUCT SUMMARY						
Package	TO-220AC, TO-220FP					
I <sub>F(AV)</sub>	8 A					
$V_{R}$	600 V					
V <sub>F</sub> at I <sub>F</sub>	1.3 V					
t <sub>rr</sub> typ.	18 ns					
T <sub>J</sub> max.	175 °C					
Diode variation	Single die					

#### **FEATURES**

- · Hyperfast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- Fully isolated package (V<sub>INS</sub> = 2500 V<sub>RMS</sub>)
- UL E78996 approved



· Designed and qualified according to JEDEC®-JESD 47

· Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>







**FREE** 

### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Repetitive peak reverse voltage		$V_{RRM}$		600	V		
Average rectified forward current		I <sub>F(AV)</sub>	T <sub>C</sub> = 144 °C	- 8			
	FULL-PAK		T <sub>C</sub> = 108 °C				
Name and the second sec			T <sub>J</sub> = 25 °C	90	Α		
Non-repetitive peak surge current	FULL-PAK	I <sub>FSM</sub>		100			
Repetitive peak forward current		I <sub>FM</sub>		16			
Operating junction and storage temp	eratures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C		

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	Ι <sub>R</sub> = 100 μΑ	600	-	-			
Forward voltage	$V_{F}$	I <sub>F</sub> = 8 A	-	2.0	2.4	V		
		I <sub>F</sub> = 8 A, T <sub>J</sub> = 150 °C	-	1.3	1.8			
December 1 and 1 a		$V_R = V_R$ rated	-	0.3	50			
Reverse leakage current	I <sub>R</sub>	$T_J = 150 ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	55	500	μA		
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V	=	17	-	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH		

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST	CONDITIONS	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1 A, dI_F/dt = 100$	$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		18	22		
Poverse recovery time		$I_F = 8 \text{ A}, dI_F/dt = 100$	$I_F = 8 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		20	25		
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	25	-	ns	
		T <sub>J</sub> = 125 °C	I <sub>F</sub> = 8 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 390 V	=	40	-		
Peak recovery current		T <sub>J</sub> = 25 °C		-	2.4	-	Α	
	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	4.8	-	^	
Dougrap vacavany abavas	0	T <sub>J</sub> = 25 °C		=	25	-	C	
Reverse recovery charge	$Q_{rr}$	T <sub>J</sub> = 125 °C		=	120	-	nC	
Reverse recovery time	t <sub>rr</sub>		I <sub>F</sub> = 8 A	-	33	-	ns	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	dl <sub>F</sub> /dt = 600 A/μs	-	12	-	Α	
Reverse recovery charge	Q <sub>rr</sub>		$V_{R} = 390 \text{ V}$	-	220	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	BOL TEST CONDITIONS		TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C		
Thermal resistance,	D.,		-	1.4	2			
junction to case (FULL-PAK)	$R_{thJC}$		-	3.4	4.3			
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>	Typical socket mount	-	-	70	°C/W		
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-			
\\/-:			-	2.0	-	g		
Weight			-	0.07	-	OZ.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Mayling daving		Case style TO-220AC	8ETH06					
Marking device		Case style TO-220 FULL-PAK		8ETH	I06FP			

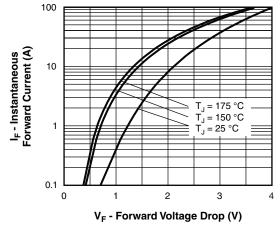


Fig. 1 - Typical Forward Voltage Drop Characteristics

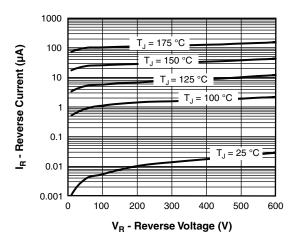


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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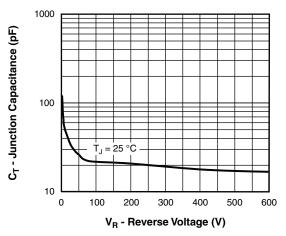


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

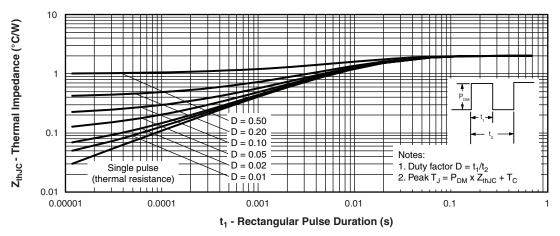


Fig. 4 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics

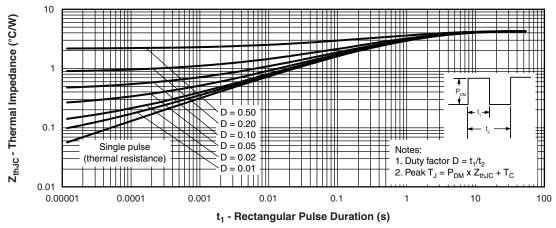


Fig. 5 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics (FULL-PAK)



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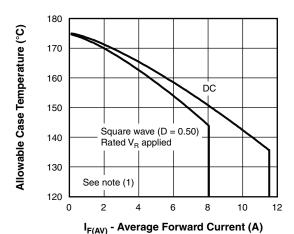


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current

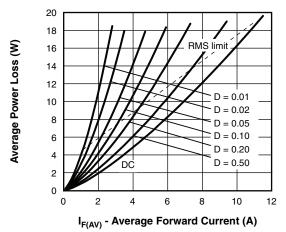


Fig. 8 - Forward Power Loss Characteristics

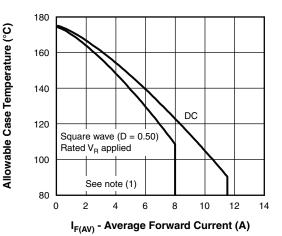


Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)

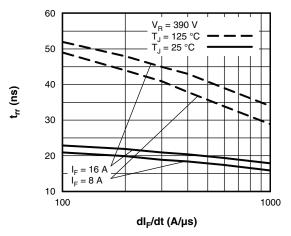


Fig. 9 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

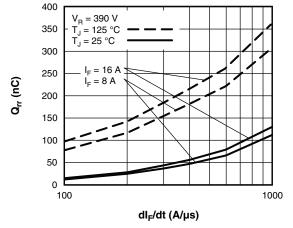


Fig. 10 - Typical Stored Charge vs. dl<sub>F</sub>/dt

### Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{th,JC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 8)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{Rated } V_R \\ \end{array}$ 

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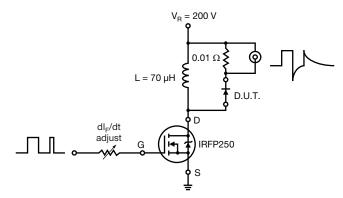
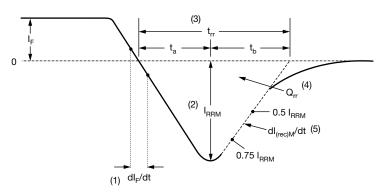


Fig. 11 - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm l_{F}$  to point where a line passing through 0.75  $\rm l_{RRM}$  and 0.50  $\rm l_{RRM}$  extrapolated to zero current.
- (4)  $\boldsymbol{Q}_{rr}$  area under curve defined by  $\boldsymbol{t}_{rr}$  and  $\boldsymbol{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

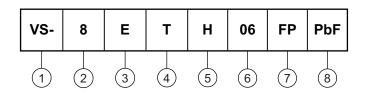
(5) dl<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 12 - Reverse Recovery Waveform and Definitions

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#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - Current rating (8 = 8 A)

3 - E = single diode

4 - T = TO-220, D<sup>2</sup>PAK

5 - H = hyperfast recovery

6 - Voltage rating (06 = 600 V)

7 - • None = TO-220AC

• FP = TO-220 FULL-PAK

8 - Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

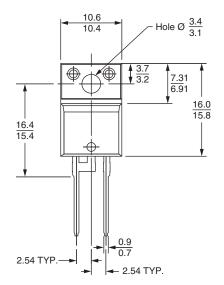
-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

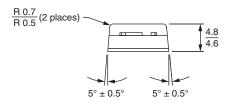
ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-8ETH06PbF	50	1000	Antistatic plastic tube					
VS-8ETH06-N3	50	1000	Antistatic plastic tube					
VS-8ETH06FPPbF	50	1000	Antistatic plastic tube					
VS-8ETH06FP-N3	50	1000	Antistatic plastic tube					

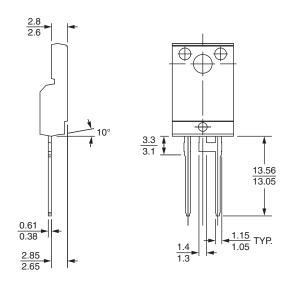
LINKS TO RELATED DOCUMENTS						
Dimensions	TO-220AC	www.vishay.com/doc?95221				
Differisions	TO-220FP	www.vishay.com/doc?95005				
Part marking information	TO-220ACPbF	www.vishay.com/doc?95224				
	TO-220AC-N3	www.vishay.com/doc?95068				
	TO-220FPPbF	www.vishay.com/doc?95009				
	TO-220FP-N3	www.vishay.com/doc?95440				

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### **DIMENSIONS** in millimeters







#### Lead assignments

Diodes

1 + 2 - Cathode

3 - Anode

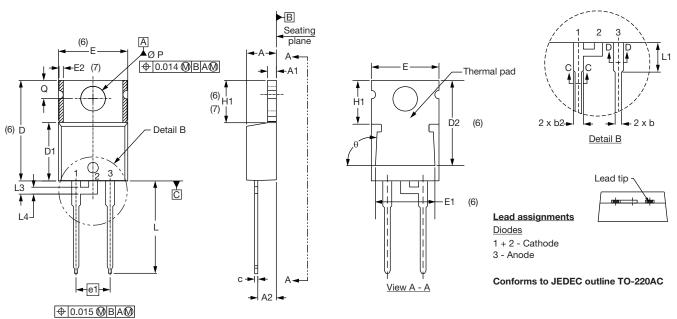
Conforms to JEDEC outline TO-220 FULL-PAK



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### **TO-220AC**

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIM	MILLIMETERS		INCHES	
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
Е	10.11	10.51	0.398	0.414	3, 6

CVMPOL	SYMBOL MILLIMETERS INCH		HES	NOTES	
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
L3	1.78	2.13	0.070	0.084	
L4	0.76	1.27	0.030	0.050	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° t	o 93°	90° t	o 93°	
		•		•	•

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline



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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

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